



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

1PW

Docket No.: AMD-H0634

I hereby certify that this transmittal of the below described document is being deposited with the United States Postal Service in an envelope bearing Prepaid Postage and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the below date of deposit:

Date of Deposit:	10/07/04	Name of Person Making the Deposit:	Shannon Carmo	Signature of the Person Making the Deposit:	<i>Shannon Carmo</i>
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Inventor(s): Shenqing FANG

Serial No.: 10/661,720

Group Art Unit: 2818

Filed: 09/11/2003

Examiner:

Confirmation No: 8251

Title: FLASH MEMORY CELL DRAIN AND SOURCE FABRICATION METHOD AND SYSTEM

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

TRANSMITTAL OF FORMAL DRAWINGS

In response to Drawing Informalities

attached please find:

☒ (a) the formal drawings for this application
Number of Sheets 6

Each sheet of drawing indicates the identifying indicia suggested in § 1.84(c) on the reverse side of the drawing

☐ (b) a copy of the NOTICE OF INFORMAL DRAWINGS

Please direct all correspondence concerning the above-identified application to the following address:

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Respectfully submitted,

Date: October 7, 2004

By: *John F. Ryan*
John F. Ryan
Reg. No. 47,050